



09/662,682

PATENT APPLICATION

#6/A  
7/1/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Li et al.

Serial No.: 09/662,682

Filed: September 15, 2000

For: METAL-ASSISTED CHEMICAL  
ETCH POROUS SILICON  
FORMATION METHOD

Art Unit: 1765

Examiner: Vinh, Lan

)  
) I hereby certify that this paper is being deposited with  
) the United States Postal Service as FIRST-CLASS mail  
) in an envelope addressed to: Assistant Commissioner  
) for Patents, Washington, D.C. 20231, on this date.

) 6/13/02  
) Date  
) F-CLASS.WCM  
) Appr. February 20, 1998

Registration No. 35132

Attorney for Applicant

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AMENDMENT A

Assistant Commissioner for Patents  
Washington, D.C. 20231

RECEIVED

JUN 25 2002

TC 1700

Dear Sir:

In response to the office action mailed March 13, 2002, please amend the  
application as follows:

In the Specification:

Please replace the paragraph beginning on page 1, line 3 with the following  
re-written paragraph:

--STATEMENT OF GOVERNMENT INTEREST

A1